

Please substitute the abstract on page 30 - 31 with the following:

ABSTRACT

A reinforced semiconductor interconnect structure, having the following components:

(1) A first metal interconnect disposed in a first material, the first metal interconnect having a line portion and at least one via portion, an anode section and a cathode section, the via portion of the first metal interconnect located in the anode section, the line portion of the first metal interconnect having a top, bottom and terminus side, wherein at least a part of the bottom side of the line portion of the first metal interconnect in contact with the first dielectric; and

(2) a first reinforcement disposed in the first material, the first reinforcement in contact with at least the bottom side of the first metal interconnect, the first reinforcement comprising a second material, the second material being electrically nonconductive; and wherein the second material has a greater mechanical rigidity than the first material.